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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO
10/029,144	12/28/2001	Hye Young Kim	2658-0275P	5231
2292 75	90 10/24/2005		EXAMINER	
	ART KOLASCH & BI	QI, ZHI QIANG		
PO BOX 747 FALLS CHURG	CH, VA 22040-0747		ART UNIT	PAPER NUMBER
	,		2871	

DATE MAILED: 10/24/2005

Please find below and/or attached an Office communication concerning this application or proceeding.

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	Application No.	Applicant(s)	
5. ÷	10/029,144	KIM ET AL.	
Office Action Summary	Examiner	Art Unit	
	Mike Qi	2871	
The MAILING DATE of this communication	appears on the cover sheet w	ith the correspondence addre	ss
Period for Reply	DI V IO OET TO EVOIDE 6 A	ONTHIO OF THEFTY (20)	2470
A SHORTENED STATUTORY PERIOD FOR REI WHICHEVER IS LONGER, FROM THE MAILING - Extensions of time may be available under the provisions of 37 CFR after SIX (6) MONTHS from the mailing date of this communication. - If NO period for reply is specified above, the maximum statutory peri - Failure to reply within the set or extended period for reply will, by sta Any reply received by the Office later than three months after the may earned patent term adjustment. See 37 CFR 1.704(b).	DATE OF THIS COMMUNI 1.136(a). In no event, however, may a iod will apply and will expire SIX (6) MOI tute, cause the application to become A	CATION. reply be timely filed NTHS from the mailing date of this committee BANDONED (35 U.S.C. § 133).	
Status	•		
Responsive to communication(s) filed on 21 This action is FINAL . 2b)⊠ T Since this application is in condition for allow closed in accordance with the practice under	his action is non-final. wance except for formal mat	•	erits is
Disposition of Claims			:
4)	Irawn from consideration.		
Application Papers			i
9)☐ The specification is objected to by the Exam	iner.		
10) The drawing(s) filed on is/are: a) □ a	accepted or b) objected to	by the Examiner.	
Applicant may not request that any objection to t	he drawing(s) be held in abeya	nce. See 37 CFR 1.85(a).	
Replacement drawing sheet(s) including the corr	·	` •	` '
11) The oath or declaration is objected to by the	Examiner. Note the attache	d Office Action or form PTO-	152.
Priority under 35 U.S.C. § 119		•	
12) Acknowledgment is made of a claim for foreign a) All b) Some * c) None of: 1. Certified copies of the priority docume 2. Certified copies of the priority docume 3. Copies of the certified copies of the papplication from the International Bure * See the attached detailed Office action for a least term of the papplication from the least term of the papplication for a least t	ents have been received. ents have been received in A riority documents have been eau (PCT Rule 17.2(a)).	opplication No received in this National Sta	ge
Attachment(s)			
Notice of References Cited (PTO-892)		Summary (PTO-413)	
 Notice of Draftsperson's Patent Drawing Review (PTO-948) Information Disclosure Statement(s) (PTO-1449 or PTO/SB/Paper No(s)/Mail Date 		s)/Mail Date nformal Patent Application (PTO-15: 	2)

Art Unit: 2871

DETAILED ACTION

A request for continued examination under 37 CFR 1.114, including the fee set forth in 37 CFR 1.17(e), was filed in this application after final rejection. Since this application is eligible for continued examination under 37 CFR 1.114, and the fee set forth in 37 CFR 1.17(e) has been timely paid, the finality of the previous Office action has been withdrawn pursuant to 37 CFR 1.114. Applicant's submission filed on Sep.21, 2005 has been entered.

Claim Rejections - 35 USC § 103

- 1. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:
 - (a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.
- 2. Claims 22 and 23 are rejected under 35 U.S.C. 103(a) as being unpatentable over US 6,001,539 (Lyu et al) in view of US 5,135,581 (Tran et al), US 5,628,933 (Carter et al) and US 6,433,842 (Kaneko et al).

Regarding claims 22 and 23, Lyu discloses (col.1, lines 20-67; Fig. 2) that forming method of an LCD comprising:

- a substrate (11);
- a switching device (TFT) for driving the pixel electrode over the substrate
 (11);

Art Unit: 2871

depositing a protective film (passivation layer 15 and 10) over the substrate
 (11) to cover the switching device;

- defining a contact hole in the protective film (15,10) to expose the drain electrode (34) of the switching device;
- forming pixel electrode (12) to connect the drain electrode (34) via the contact hole.

Lyn does not explicitly disclose that:

- 1) the pixel electrode is formed by placing the substrate in a vacuum chamber and injecting hydrogen-containing gas at a temperature of less than 400 °C, and the substrate has a temperature of less than about 200 °C when forming the pixel electrode;
 - 2) the pixel electrode has an amorphous structure.

Tran discloses (col.2, line 20 - col.4, line 58) forming an electrically conductive oxide composition used as a light transmissive electrode in a device, such as liquid crystal displays, by sputtering at temperature from 20 °C to 300 °C (less than 400 °C) with stabilizing gas such as H₂ or H₂O (hydrogen-containing gas), and preferably, the sputter depositing occurs at temperature of from 25 °C to 150 °C. Inherently, the substrate must be placed in a vacuum chamber. Tran further discloses (col.2, line 64 – col.3, line 6) that forming electrode using a room temperature process allows liquid crystal display to be prepared on a supports (substrate) which would otherwise be damaged by high temperature processes (preventing the damage by high temperature processes).

Art Unit: 2871

The depositing includes conductive electrodes depositing on a substrate, so that the substrate has a temperature less than 200 °C according to the room temperature process. The pixel electrode also is a conductive electrode. The forming process for a conductive electrode is also suitable for the pixel electrode in order to prevent the damage by high temperature processes. Less than 400°C can be any degree as long as less than 200°C

As an evidence, **Cater** discloses (col. 1, lines 31-41; col.4, lines 16-38) that a transparent conductor forming method (deposition process) in which the substrate in a vacuum chamber was heated to 250 °C, and after growth of several thousand angstroms, the chamber was again evacuated and the substrate was permitted to cool to room temperature (i.e., less than 200 °C), and the film subsequently removed from the chamber has good electrical conductivity. According to the specification of the paragraph 0035 of this application, the depositing process allows the substrate temperature to be less than about 200 °C. Therefore, the substrate in the deposition process was also permitted to a cool temperature to be less than 200 °C, and the reference Cater reads this process in which the substrate was permitted to room temperature (less than 200 °C).

Lyn, Tran and Cater teach the invention set firth above except for the pixel electrode has an amorphous structure, and the pixel electrode is etched with a weak acid etchant.

Kaneko discloses (col.5, lines 47 – 51) that the pixel electrode has an

Art Unit: 2871

amorphous structure, because using amorphous indium tin oxide (ITO) or indium zinc oxide (IZO) as the material of the pixel electrodes. Kaneko further discloses (col.9, lines 7 – 43) that by using the weak acid, the layered structure underlying the ITO film is secured from being damaged during the etching of the ITO film.

Therefore, it would have been obvious to those skilled in the art at the time the invention was made to modify the liquid crystal display of Lyn with the teachings of a forming process such as injecting hydrogen-containing gas at a temperature less than 400 °C and the substrate has a temperature of less than 200 °C and the pixel electrode having amorphous structure with weak acid etchant as taught by Tran, Cater and Kaneko, since the skilled in the art would be motivated for preventing the damage by high temperature processes and securing the electrodes underlying the pixel electrodes from being damaged during etching.

Allowable Subject Matter

- 3. Claims 1,3, 6-13 and 15-18 are allowed.
- 4. The following is a statement of reasons for the indication of allowable subject matter:

The prior art of record neither discloses nor teaches that forming pixel electrode in a liquid crystal display comprises various steps, more specifically, as the following:

the substrate has a temperature between about 50°C and about 150°C and the substrate temperature being half the temperature of the vacuum chamber [claims 1 and 13].

Application/Control Number: 10/029,144 Page 6

Art Unit: 2871

The closest references such as Tran, Cater disclose forming conductive electrode by sputtering at a temperature from 20 °C to 300°C, and the electrode being formed on a substrate using lower temperature such as room temperature to prevent the high temperature damage. However, the prior art of record do not specifically discloses that the substrate has a temperature between about 50°C and about 150°C and the substrate temperature being half the temperature of the vacuum chamber.

Response to Arguments

- 5. Applicant's arguments filed on Sep.21, 2005 have been fully considered but they are not persuasive.
- 1) The reference Tran discloses (col.2, line 20 col.4, line 58) forming an electrically conductive oxide composition used as a light transmissive electrode in a device, such liquid crystal displays, by sputtering at temperature from 20 °C to 300 °C (less as than 400 °C) with stabilizing gas such as H₂ or H₂O (hydrogen-containing gas), and forming electrode using a room temperature process allows liquid crystal display to be prepared on a supports (substrate) which would otherwise be damaged by high temperature processes (preventing the damage by high temperature processes). Less than 400°C can be any degree as long as less than 400°C and less than 200°C can be any degree as long as less than 200°C.

Art Unit: 2871

Conclusion

6. The prior art made of record and not relied upon is considered pertinent to applicant's disclosure.

1) As an evidence, US 6,466,293 (Suzuki et al) discloses (col.19, line 43 – col.20, line 32) that a LCD forming process in which the substrates precisely superposed and adhered and then were placed in a vacuum chamber.

7. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Mike Qi whose telephone number is (571) 272-2299. The examiner can normally be reached on M-T 8:00 am-5:00 pm.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Robert Kim can be reached on (571) 272-2293. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

Mike Qi October 18, 2005

ANDREW SCHECHTER
PRIMARY EXAMINER

Page 7